

Standard specifications of $\Phi 2$ inch HVPE β -Ga₂O₃ epitaxial wafers

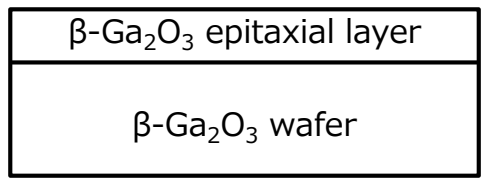
Epitaxial layer (Growth method: HVPE)

Property	Specification
Dopant	Si (n-type)
Doping concentration	Specify a value in the range between 2×10^{16} and $9 \times 10^{16} \text{ cm}^{-3}$
Thickness	Specify a value in the range between 5 and 10 μm

Property	Specification
Dopant	Sn (n-type)
Doping concentration	$1\text{-}20 \times 10^{18} \text{ cm}^{-3}$
Orientation	(001)
Size	$\Phi 2$ inch
Thickness	0.65 mm
XRD FWHM	≤ 350 arcsec
Off set angle	$0^\circ \pm 1^\circ$

Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.



Cross section of Gallium oxide epitaxial wafers

